

AMENDMENT UNDER 37 C.F.R. § 1.111
U.S. Application No. 09/315,068

5. (New) A semiconductor laser as defined in Claim 1, wherein the upper and lower optical waveguide layers on opposite sides of the quantum well layer are different thicknesses.

6. (New) A semiconductor laser as defined in Claim 1, wherein a thickness of the upper cladding layer is greater than zero, but less than or equal to $1\mu\text{m}$.
